

80 V, single N-channel Trench MOSFET 17 December 2013

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quid	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	80	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V_{GS} = 10 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	-	4.1	А
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 2.8 A; T _j = 25 °C		-	80	105	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		D
2	D	drain		
3	G	gate		G (The second s
4	S	source		
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	S 017aaa255
7	D	drain		
8	S	source		

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PMPB95ENEA	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

7. Marking

Table 4. Marking codes	
Type number	Marking code
PMPB95ENEA	2A

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	80	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	4.1	А
		V_{GS} = 10 V; T_{amb} = 25 °C	[1]	-	2.8	А
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	1.8	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	11.2	А

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Symbol	Parameter	Conditions		Min	Мах	Unit	
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 0.46 A; DUT in avalanche (unclamped)		-	19.3	mJ	
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.6	W	
		T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.3	W	
		T _{sp} = 25 °C		-	15.6	W	
Tj	junction temperature			-55	150	°C	
T _{amb}	ambient temperature			-55	150	°C	
T _{stg}	storage temperature			-65	150	°C	
Source-drain	diode	1				,	
I _S	source current	T _{amb} = 25 °C	[1]	-	1.2	А	
ESD maximum rating							
V _{ESD}	electrostatic discharge voltage	HBM	[2]	-	2000	V	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Measured between all pins.

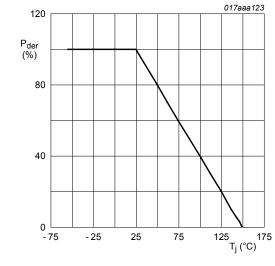


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

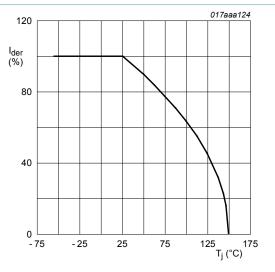


Fig. 2. Normalized continuous drain current as a function of junction temperature

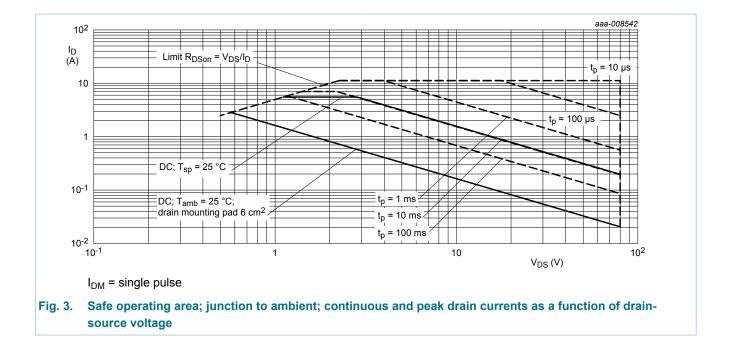
$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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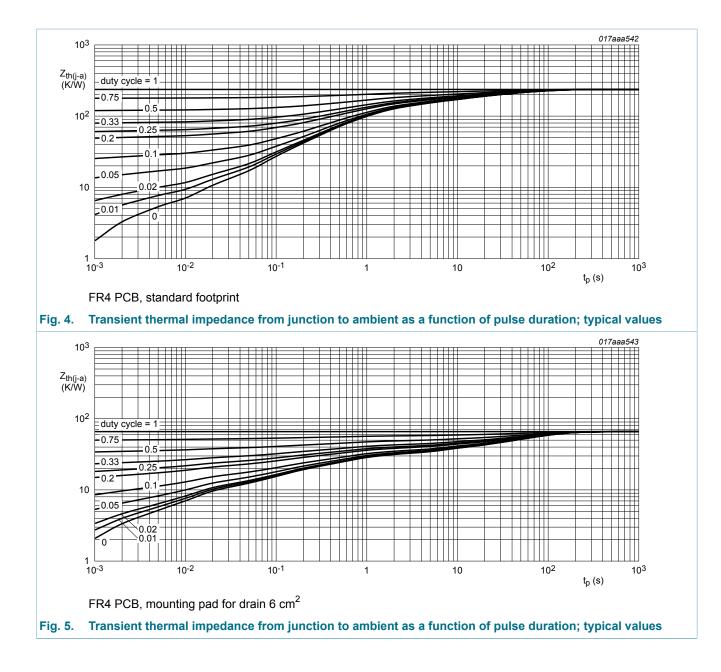


9. Thermal characteristics

Table 6. 1	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui(j-α)	thermal resistance		[1]	-	239	275	K/W
	from junction to ambient		[2]	-	67	77	K/W
	ampient	in free air; t ≤ 5 s	[2]	-	33	38	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	4	8	K/W

Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
 Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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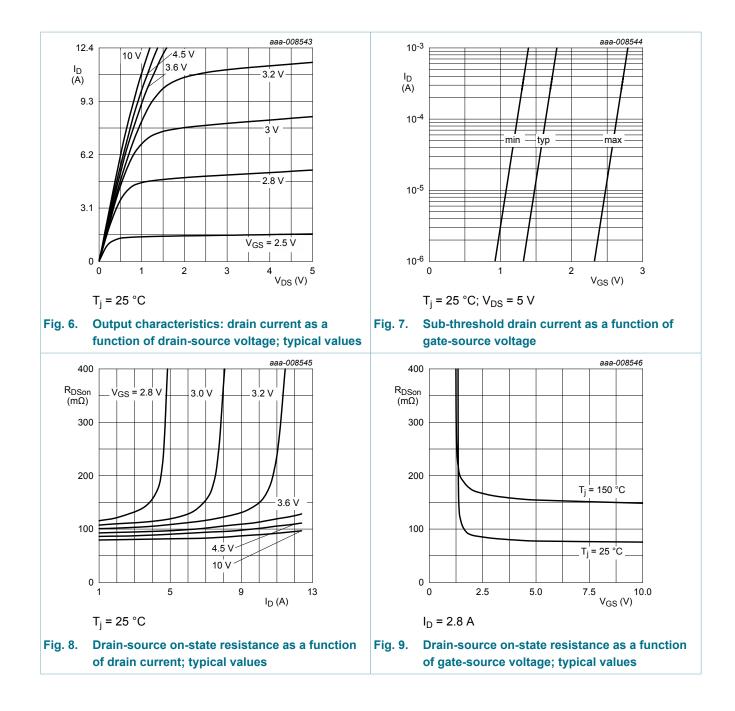


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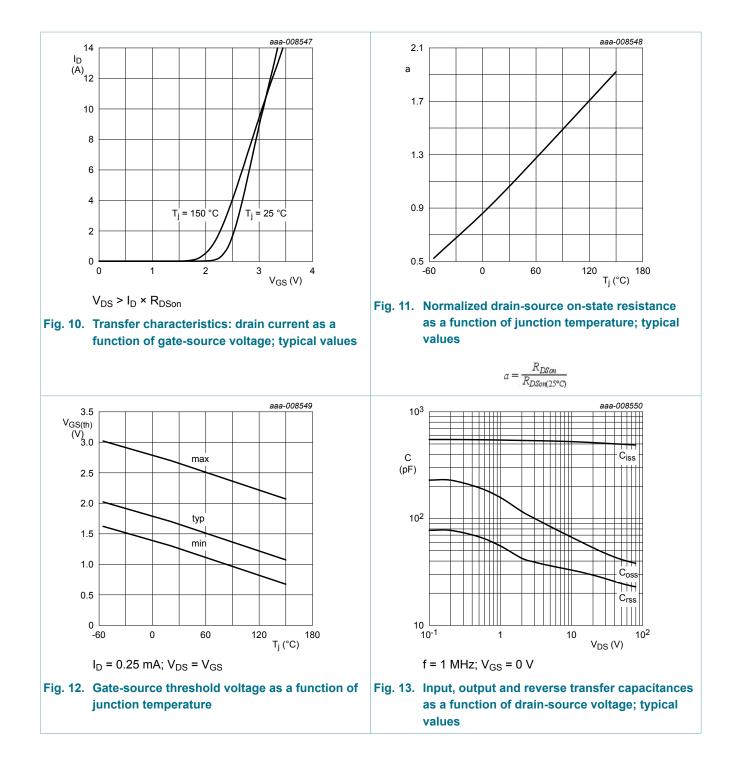
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	80	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = 250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	1.3	1.7	2.7	V
I _{DSS}	drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μA
		V_{DS} = 80 V; V_{GS} = 0 V; T_j = 150 °C	-	-	10	μA
I _{GSS} gate leakag	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	10	μA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-10	μA
		V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	1	μA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-1	μA
Doon	drain-source on-state	V_{GS} = 10 V; I _D = 2.8 A; T _j = 25 °C	-	80	105	mΩ
	resistance	V _{GS} = 10 V; I _D = 2.8 A; T _j = 150 °C	-	154	202	mΩ
		V_{GS} = 4.5 V; I _D = 2.6 A; T _j = 25 °C	-	92	120	mΩ
9 _{fs}	forward transconductance	V_{DS} = 10 V; I _D = 2.8 A; T _j = 25 °C	-	13.3	-	S
R _G	gate resistance	f = 1 MHz	-	4.7	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = 40 V; I _D = 2.8 A; V _{GS} = 10 V;	-	9.9	14.9	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.2	-	nC
Q _{GD}	gate-drain charge		-	1.8	-	nC
C _{iss}	input capacitance	V_{DS} = 40 V; f = 1 MHz; V_{GS} = 0 V;	-	504	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	43	-	pF
C _{rss}	reverse transfer capacitance		-	26	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 40 V; I _D = 2.8 A; V _{GS} = 10 V;	-	5	-	ns
t _r	rise time	R _{G(ext)} = 6 Ω; T _j = 25 °C	-	4	-	ns
t _{d(off)}	turn-off delay time		-	15	-	ns
t _f	fall time		-	7	-	ns
Source-drai	n diode		I			
V _{SD}	source-drain voltage	I _S = 1.2 A; V _{GS} = 0 V; T _i = 25 °C	-	0.8	1.2	V

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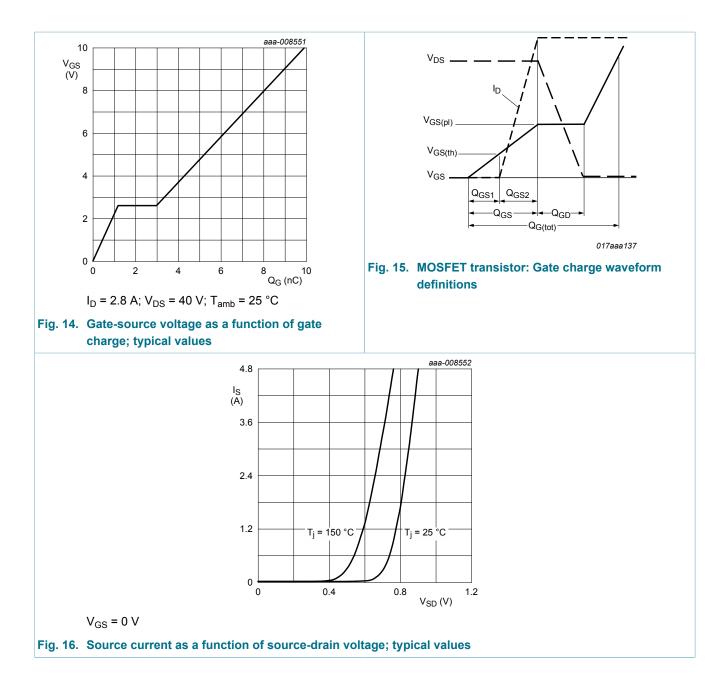


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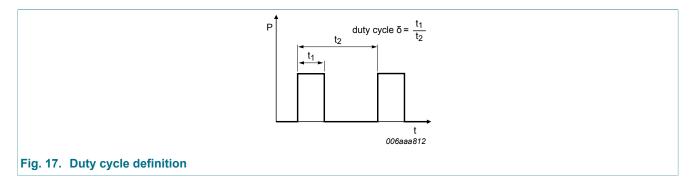
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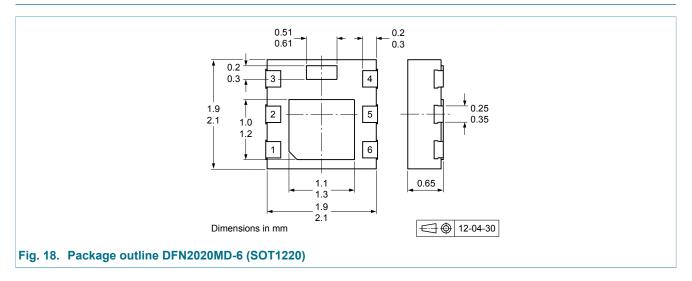
11. Test information



11.1 Quality information

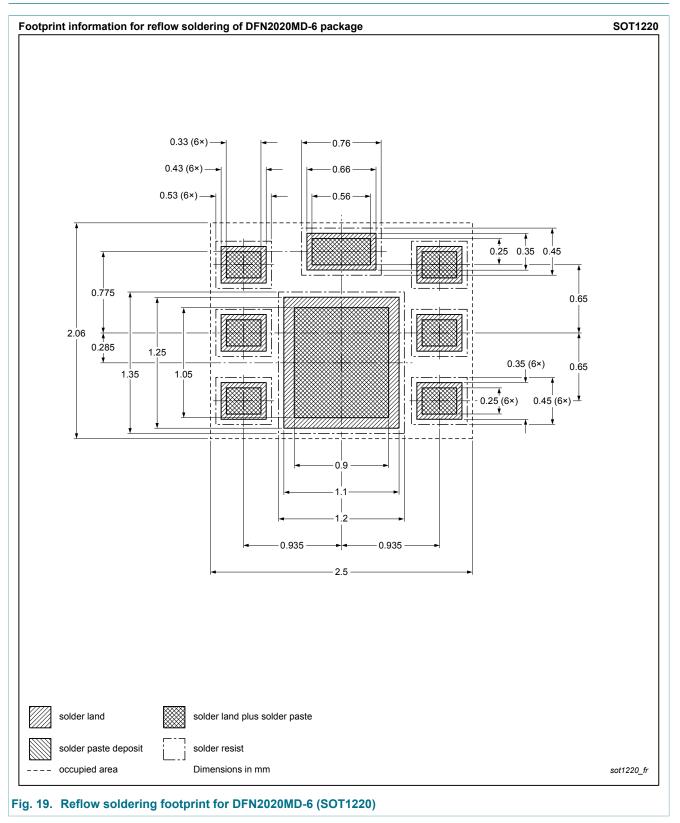
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMPB95ENEA v.2	20131217	Product data sheet	-	PMPB95ENEA v.1			
Modifications:	Product status char	nged	·				
PMPB95ENEA v.1	20130218	Objective data sheet	-	-			

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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